

6. (Amended) The semiconductor laser as claimed in claim 3, further comprising a dielectric film provided between the [laser beam-emitting end facet] laser beam-emitting facet and the light-shielding film, part of the dielectric film being exposed at the small opening.
7. (Amended) The semiconductor laser as claimed in claim 4, further comprising a dielectric film provided between the [laser beam-emitting end facet] laser beam-emitting facet and the light-shielding film, part of the dielectric film being exposed at the small opening.
8. (Amended) A method of producing a semiconductor laser having a [laser beam-emitting end facet] laser beam-emitting facet including a laser beam-emitting region comprising a step of forming a three-dimensional feature portion at a location on the [laser beam-emitting end facet] laser beam-emitting facet to have a prescribed relationship with the light-emitting region.
11. (Amended) The method as claimed in claim 8, further comprising a step of irradiating at least the light-emitting region of the [laser beam-emitting end facet] laser beam-emitting facet with a focused ion beam before the step of forming the three-dimensional feature portion.
12. (Amended) The method as claimed in claim 9, further comprising a step of irradiating at least the light-emitting region of the [laser beam-emitting end facet] laser beam-emitting facet with a focused ion beam before the step of forming the three-dimensional feature portion.
13. (Amended) The method as claimed in claim 10, further comprising a step of irradiating at least the light-emitting region of the [laser beam-emitting end facet] laser beam-emitting facet with a focused ion beam before the step of forming the three-dimensional feature portion.